

Please amend the claims as follows:

F1 sub H1 23. (Amended) An operable gate stack, including a non-crystalline metallic silicide film.

F2 sub H1 24. (Thrice Amended) An operable gate stack, including an amorphous metallic silicide film wherein said metallic silicide film is substantially devoid of silicon clusters.

25. (Thrice Amended) An operable gate stack on a silicon substrate having a dielectric layer thereover, comprising:

a polysilicon layer disposed over said dielectric layer;

a non-crystalline metallic silicide film disposed over said polysilicon layer; and

a dielectric cap on said non-crystalline metallic silicide film.

F3 sub H1 26. (Twice Amended) A gate stack structure comprising an operable gate stack on a dielectric layer, over a silicon substrate, wherein said dielectric layer is substantially devoid of pitting.

F4 sub H1 27. (Amended) The gate stack structure of claim 26 wherein said operable gate stack includes a non-crystalline metallic silicide film.

F5 sub H1 28. (Previously Twice Amended) The gate stack structure of claim 26 wherein said operable gate stack includes an amorphous metallic silicide film substantially devoid of silicon clusters.

Please add claims 29 through 33 as follows:

sub G15
29. A semiconductor device, comprising at least one gate stack having a non-crystalline metallic silicide film.

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30. The semiconductor device of claim 29, wherein said at least one gate stack comprises:

a silicon substrate having a dielectric layer thereover;

a polysilicon layer disposed over said dielectric layer;

a non-crystalline metallic silicide film disposed over said polysilicon layer; and

a dielectric cap on said non-crystalline metallic silicide film.

31. A semiconductor device, comprising at least one gate stack structure on a dielectric layer, over a silicon substrate, wherein said dielectric layer is substantially devoid of pitting.

32. The semiconductor device of claim 31, wherein said at least one gate stack structure includes a non-crystalline metallic silicide film.

33. The semiconductor device of claim 31, wherein said at least one gate stack structure includes an amorphous silicide film substantially devoid of silicon clusters.